

6367254 MOTOROLA SC (XSTRS/R F)

96D-80721 D

T-33-13

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA
BUS47
BUS47A
SWITCHMODE II^Δ SERIES
NPN SILICON POWER TRANSISTORS

The BUS 47 and BUS 47A transistors are designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line-operated switch-mode applications such as:

- Switching Regulators
- Inverters
- Solenoid and Relay Drivers
- Motor Controls
- Deflection Circuits

Fast Turn-Off Times

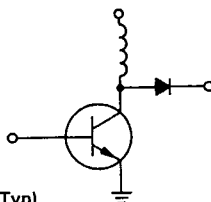
60 ns Inductive Fall Time—25°C (Typ)

120 ns Inductive Crossover Time—25°C (Typ)

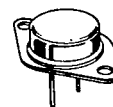
Operating Temperature Range -65 to +200°C

100°C Performance Specified for:

- Reverse-Biased SOA with Inductive Loads
- Switching Times with Inductive Loads
- Saturation Voltages
- Leakage Currents (125°C)


9 AMPERES
NPN SILICON
POWER TRANSISTORS
400 AND 450 VOLTS (BVCEO)
150 WATTS
850 - 1000 V (BVCEs)
Designer's Data for
"Worst Case" Conditions

The Designers^Δ Data Sheet permits the design of most circuits entirely from the information presented. Limit data — representing device characteristics boundaries — are given to facilitate "worst case" design.

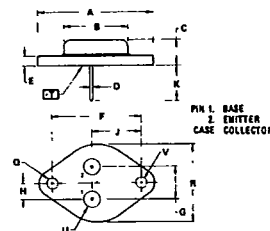

MAXIMUM RATINGS

Rating	Symbol	BUS 47	BUS 47A	Unit
Collector-Emitter Voltage	$V_{CE(sus)}$	450	450	Vdc
Collector-Emitter Voltage	V_{CEV}	850	1000	Vdc
Emitter Base Voltage	V_{EB}	7		Vdc
Collector Current — Continuous	I_C	9		Adc
— Peak (1)	I_{CM}	18		
— Overload	I_{OI}	36		
Base Current — Continuous	I_B	5		Adc
— Peak (1)	I_{BM}	10		
Total Power Dissipation — $T_C = 25^\circ\text{C}$	P_D	150		Watts
— $T_C = 100^\circ\text{C}$		85.5		
Derate above 25°C		0.86		W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.17	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	275	°C

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.



NOTES
 1. DIMENSIONS Q AND V ARE DATUMS
 2. [] IS SEATING PLANE AND DATUM
 3. POSITIONAL TOLERANCE FOR MOUNTING HOLE D
 4. DIMENSIONS AND TOLERANCES PER ANSI Y14.5, 1973

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	35.27	—	1.350
B	—	21.08	—	0.830
C	6.35	7.62	0.250	0.300
D	0.91	1.27	0.036	0.050
E	1.43	1.78	0.055	0.070
F	30.15 BSC		1.187 BSC	
G	10.92 BSC		0.430 BSC	
H	5.48 BSC		0.215 BSC	
J	16.49 BSC		0.649 BSC	
K	11.18	12.19	0.442	0.480
L	3.81	4.19	0.150	0.165
M	—	26.67	—	1.050
N	4.83	5.33	0.190	0.210
V	3.81	4.19	0.150	0.165

CASE 1-05 TO-3 TYPE

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96D 80722 D

BUS47, BUS47A

T-33-13

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (1)					
Collector-Emitter Sustaining Voltage (Table 1) ($I_C = 200\text{ mA}$, $I_B = 0$) $L = 25\text{ mH}$	BUS47 BUS47A	$V_{CE(sus)}$	400 450	—	Vdc
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$) ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{ Vdc}$, $T_C = 125^\circ\text{C}$)		I_{CEV}	— —	0.15 1.5	mAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEV}$, $R_{BE} = 10\ \Omega$)	$T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	I_{CER}	— —	0.4 3.0	mAdc
Emitter Cutoff Current ($V_{EB} = 5\text{ Vdc}$, $I_C = 0$)		I_{EBO}	—	0.1	mAdc
Emitter-base breakdown Voltage ($I_E = 50\text{ mA}$, $I_C = 0$)		$BVEBO$	7.0	—	Vdc

SECOND BREAKDOWN

Second Breakdown Collector Current with Base Forward Biased	$I_{S/b}$	See Figure 12	
Clamped Inductive SOA with Base Reverse Biased	$RBSOA$	See Figure 13	

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 6\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 5\text{ Adc}$, $V_{CE} = 5\text{ V}$)	BUS47 BUS47A	h_{FE}	7	—	—	
Collector-Emitter Saturation Voltage ($I_C = 6\text{ Adc}$, $I_B = 1.2\text{ Adc}$) ($I_C = 9\text{ Adc}$, $I_B = 1.8\text{ Adc}$) ($I_C = 6\text{ Adc}$, $I_B = 1.2\text{ Adc}$, $T_C = 100^\circ\text{C}$) ($I_C = 5\text{ Adc}$, $I_B = 1\text{ Adc}$) ($I_C = 8\text{ Adc}$, $I_B = 1.6\text{ Adc}$) ($I_C = 5\text{ Adc}$, $I_B = 1\text{ Adc}$, $T_C = 100^\circ\text{C}$)	BUS47 BUS47A	$V_{CE(sat)}$	— — — — — —	— — — — — —	1.5 5.0 2.5 1.5 5.0 2.5	Vdc
Base-Emitter Saturation Voltage ($I_C = 6\text{ Adc}$, $I_B = 1.2\text{ Adc}$) ($I_C = 6\text{ Adc}$, $I_B = 1.2\text{ Adc}$, $T_C = 100^\circ\text{C}$) ($I_C = 5\text{ Adc}$, $I_B = 1\text{ Adc}$) ($I_C = 5\text{ Adc}$, $I_B = 1\text{ Adc}$, $T_C = 100^\circ\text{C}$)	BUS47 BUS47A	$V_{BE(sat)}$	— — — —	— — — —	1.6 1.6 1.6 1.6	Vdc

DYNAMIC CHARACTERISTICS

Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f_{test} = 100\text{ KHz}$)	C_{ob}	—	—	300	pF
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SWITCHING CHARACTERISTICS

Resistive Load (Table 1)

Delay Time	$V_{CC} = 250\text{ Vdc}$, $I_C = 6\text{ A}$, $I_{B1} = 1.2\text{ A}$, $t_p = 30\ \mu\text{s}$, Duty Cycle 2%, $V_{BE(off)} = 5\text{ V}$	t_d	—	0.05	0.2	μs
Rise Time		t_r	—	0.5	0.8	
Storage Time		t_s	—	1	2.0	
Fall Time		t_f	—	0.2	0.4	

Inductive Load, Clamped (Table 1)

Storage Time	$I_C(pk) = 6\text{ A}$, $I_{B1} = 1.2\text{ A}$, $V_{BE(off)} = 5\text{ V}$, $V_{CE(c1)} = 250\text{ V}$	BUS47	$(T_C = 25^\circ\text{C})$	t_{sv}	—	0.9	—	μs
Fall Time				t_{fi}	—	0.06	—	
Storage Time	$I_C(pk) = 5\text{ A}$, $I_{B1} = 1\text{ A}$	BUS47A	$(T_C = 100^\circ\text{C})$	t_{sv}	—	1.0	2.5	
Crossover Time				t_c	—	0.2	0.5	
Fall Time				t_{fi}	—	0.1	0.3	

(1) Pulse Test: $PW = 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.